## This Page Is Inserted by IFW Operations and is not a part of the Official Record

## **BEST AVAILABLE IMAGES**

Defective images within this document are accurate representations of the original documents submitted by the applicant.

Defects in the images may include (but are not limited to):

- BLACK BORDERS
- TEXT CUT OFF AT TOP, BOTTOM OR SIDES
- FADED TEXT
- ILLEGIBLE TEXT
- SKEWED/SLANTED IMAGES
- COLORED PHOTOS
- BLACK OR VERY BLACK AND WHITE DARK PHOTOS
- GRAY SCALE DOCUMENTS

## IMAGES ARE BEST AVAILABLE COPY.

As rescanning documents will not correct images, please do not report the images to the Image Problem Mailbox.

FIRST NAMED INVENTOR: Xiaojun Weng et al.
TITLE: Narrow Energy Band Gap Gallium Arsenide
Nitride Semi-Conductors And An Ion-Cut-Synthesis
Method For Producing The Same

1/6

ATTY. DOCKET NO.: 65306-0094 EXPRESS MAIL NO.: EV 223960094 US

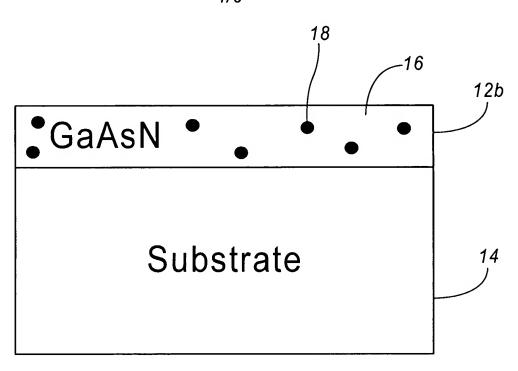


FIG. 1

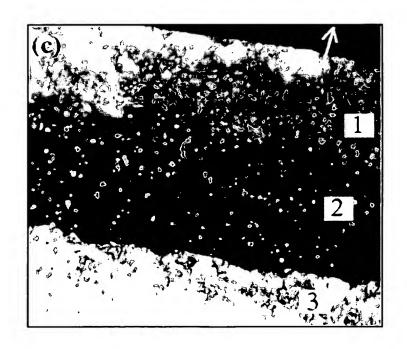


FIG. 2a

FIRST NAMED INVENTOR: Xiaojun Weng et al.
TITLE: Narrow Energy Band Gap Gallium Arsenide
Nitride Semi-Conductors And An Ion-Cut-Synthesis
Method For Producing The Same ATTY. DOCKET NO.: 65306-0094 EXPRESS MAIL NO.: EV 223960094 US

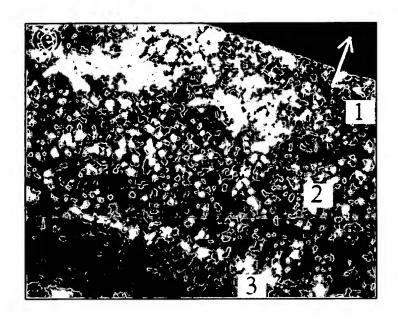


FIG. 2b

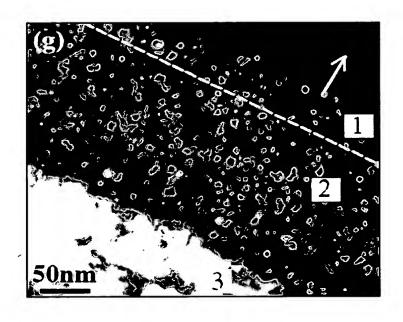


FIG. 2c

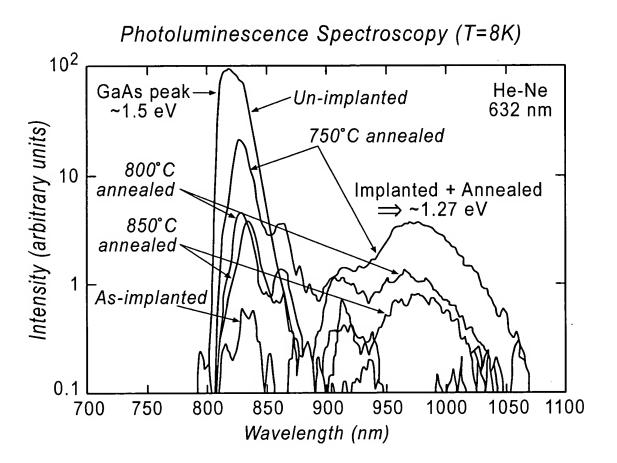
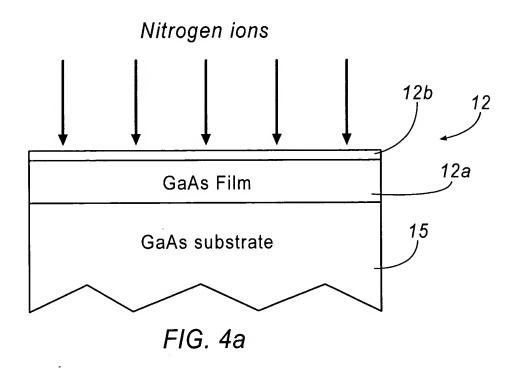
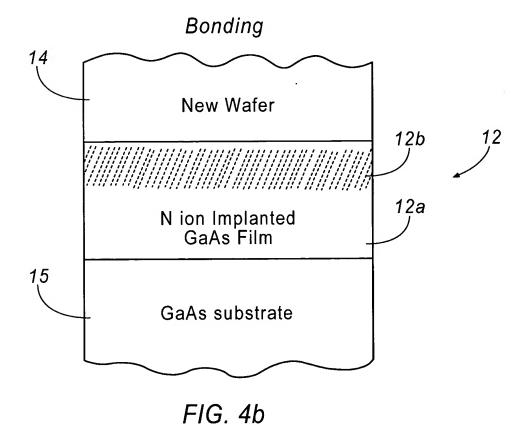


FIG. 3

ATTY. DOCKET NO.: 65306-0094 EXPRESS MAIL NO.: EV 223960094 US





FIRST NAMED INVENTOR: Xiaojun Weng et al.
TITLE: Narrow Energy Band Gap Gallium Arsenide
Nitride Semi-Conductors And An Ion-Cut-Synthesis
Method For Producing The Same

ATTY. DOCKET NO.: 65306-0094 EXPRESS MAIL NO.: EV 223960094 US

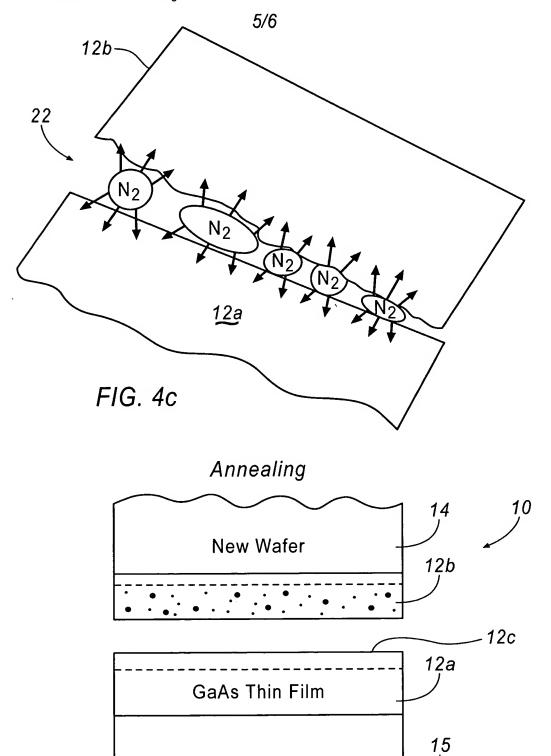


FIG. 4d

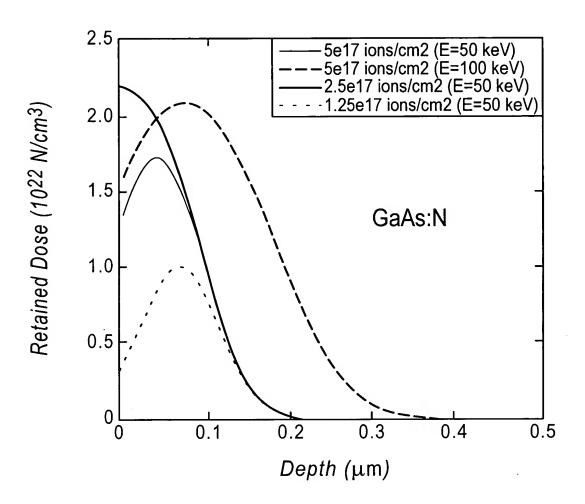


FIG. 5